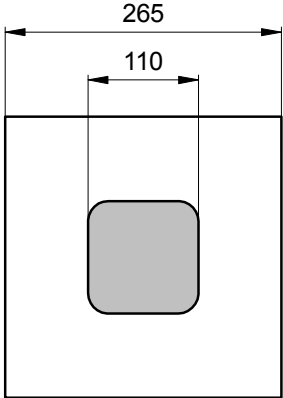


Radiation	Type	Technology	Electrodes
Yellow	Standard	AlInGaP/GaAs	P (anode) up

	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 (± 20) μm <u>cathode</u> gold alloy, 0.5 μm <u>anode</u> gold alloy, 1.5 μm	

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		2.0	2.3	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Radiant power ¹	$I_F = 20 \text{ mA}$	Φ_e	0.5	0.7		mW
Radiant power ²	$I_F = 20 \text{ mA}$	Φ_e		1.4		mW
Luminous intensity ¹	$I_F = 20 \text{ mA}$	I_V	75	110		mcd
Luminous intensity ²	$I_F = 20 \text{ mA}$	I_V		200		mcd
Peak wavelength	$I_F = 20 \text{ mA}$	λ_P	592	595	598	nm
Dominant wavelength	$I_F = 20 \text{ mA}$	λ_D		592		nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		17		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		30		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$I_V(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-590-13				

Packing: Chips on adhesive film with wire-bond side on top